L Number	Hits		DB	Time stamp
1	30635	thermal\$5 near5 treat\$3	USPAT;	2004/03/09 09:03
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
2	1120801	alignment aligning orientation orienting	USPAT;	2004/03/09 09:03
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
3	33719	source adj electrode	USPAT;	2004/03/09 09:03
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
4	33687	drain adj electrode	USPAT;	2004/03/09 09:03
-			US-PGPUB;	,
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
5	2	(thermal\$5 near5 treat\$3) same (alignment aligning orientation	USPAT;	2004/03/09 09:04
		orienting) same (source adj electrode) same (drain adj electrode)	US-PGPUB;	, ,
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
6	121	simultaneously near5 (thermal\$5 near5 treat\$3)	USPAT;	2004/03/09 09:04
			US-PGPUB;	
			EPO; JPO;	-
			DERWENT;	
			IBM_TDB	
7	1	(simultaneously near5 (thermal\$5 near5 treat\$3)) same	USPAT;	2004/03/09 09:05
		(alignment aligning orientation orienting)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
8	0	(simultaneously near5 (thermal\$5 near5 treat\$3)) and 349\$.ccls.	USPAT;	2004/03/09 09:05
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
9	11	(simultaneously near5 (thermal\$5 near5 treat\$3)) and 257\$.ccls.	USPAT;	2004/03/09 09:05
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	

L Number	Hits	Search Text	DB	Time stamp
1	551	349/141.ccls.	USPAT;	2004/03/09 07:43
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	`
			IBM_TDB	
2	661	349/187.ccls.	USPAT;	2004/03/09 07:43
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		(057/50 70)	IBM_TDB	2004/02/00 07 42
3	2063	(257/59,72).ccls.	USPAT;	2004/03/09 07:43
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM_TDB	
4	82970	(gate scan\$4) adj (line wir\$3)	USPAT;	2004/03/09 07:44
7	62970	(gate scalls+) auj (lille wills5)	US-PGPUB;	2004/03/03/03/07.44
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
5	1348093	semiconductor	USPAT;	2004/03/09 07:44
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
6	1399664	insulat\$3	USPAT;	2004/03/09 07:44
		·	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
7	48220	(pixel display picture) near2 electrode	USPAT;	2004/03/09 07:44
			US-PGPUB;	
		· ·	EPO; JPO;	
			DERWENT;	
	4220705	-h	IBM_TDB	2004/02/00 07 44
8	1338785	channel	USPAT;	2004/03/09 07:44
•			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM_TDB	
9	1141459	alignment aligning orientation orienting	USPAT;	2004/03/09 07:45
,	1111133	anginicite angining orientation orienting	US-PGPUB;	2004/03/09 07.43
			EPO; JPO;	
·			DERWENT;	
			IBM_TDB	
10	6789	thermal-treat\$3 (thermal adj treat\$3)	USPAT;	2004/03/09 07:45
			US-PGPUB;	
			EPO; JPO;	•
			DERWENT;	
			IBM_TDB	
11	53031	(source drain) adj electrode	USPAT;	2004/03/09 07:45
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
12	۱ ۵	(thormal troote) (thormal adi troote)	IBM_TDB	2004/02/00 07:46
12	4	(thermal-treat\$3 (thermal adj treat\$3)) same ((source drain) adj	USPAT;	2004/03/09 07:46
		electrode)	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM_TDB	
<u>-</u>	L	1	ם חוד ויוחד	l

•				
13	35	((gate scan\$4) adj (line wir\$3)) same semiconductor same insulat\$3 same ((pixel display picture) near2 electrode) same	USPAT; US-PGPUB;	2004/03/09 07:47
ŀ		channel same (alignment aligning orientation orienting) same	EPO; JPO;	
		((source drain) adj electrode)	DERWENT;	
		240/141 and (//asta assut4) adi (lina wint3)) assua	IBM_TDB	2004/02/00 07.47
14	4	349/141.ccls. and (((gate scan\$4) adj (line wir\$3)) same	USPAT;	2004/03/09 07:47
	İ	semiconductor same insulat\$3 same ((pixel display picture) near2	US-PGPUB;	
		electrode) same channel same (alignment aligning orientation	EPO; JPO;	
		orienting) same ((source drain) adj electrode))	DERWENT;	
45		240/107 md ///-sha seent4) adi /lina wint2)) sama	IBM_TDB	2004/02/00 07:40
15	2		USPAT;	2004/03/09 07:48
Į.	i	semiconductor same insulat\$3 same ((pixel display picture) near2	US-PGPUB;	
•		electrode) same channel same (alignment aligning orientation	EPO; JPO;	
	-	orienting) same ((source drain) adj electrode))	DERWENT;	
10	2524	((asks see #4) add (line wint3)) asms semicen ductor come	IBM_TDB	2004/02/00 07:49
16	3534	((gate scan\$4) adj (line wir\$3)) same semiconductor same	USPAT;	2004/03/09 07:48
		insulat\$3	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
17	6907	((nivel display nicture) pear? electrode) same (alignment aligning	IBM_TDB	2004/02/00 07:49
17	6897	((pixel display picture) near2 electrode) same (alignment aligning orientation orienting)	USPAT; US-PGPUB;	2004/03/09 07:48
		orientation orienting)	EPO; JPO;	
j			DERWENT;	
			IBM_TDB	
18	1505	(((gate scan\$4) adj (line wir\$3)) same semiconductor same	USPAT;	2004/03/09 07:49
10	1303	insulat\$3) same ((source drain) adj electrode)	US-PGPUB;	2007/03/03 07.73
		insulaces) same ((source drain) adj electrode)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
19	538	(((pixel display picture) near2 electrode) same (alignment aligning	USPAT;	2004/03/09 07:49
13	330	orientation orienting)) and ((((gate scan\$4) adj (line wir\$3)) same	US-PGPUB;	2001/03/03/07.13
		semiconductor same insulat\$3) same ((source drain) adj	EPO; JPO;	
		electrode))	DERWENT;	
		3.53.53.577	IBM_TDB	
20	46	349/141.ccls. and ((((pixel display picture) near2 electrode) same	USPAT;	2004/03/09 07:49
		(alignment aligning orientation orienting)) and ((((gate scan\$4)	US-PGPUB;	
1		adj (line wir\$3)) same semiconductor same insulat\$3) same	EPO; JPO;	
		((source drain) adj electrode)))	DERWENT;	
			IBM_TDB	
21	24	349/187.ccls. and ((((pixel display picture) near2 electrode) same	USPAT;	2004/03/09 07:49
		(alignment aligning orientation orienting)) and ((((gate scan\$4)	US-PGPUB;	, , ==
		adj (line wir\$3)) same semiconductor same insulat\$3) same	EPO; JPO;	
		((source drain) adj electrode)))	DERWENT;	
			IBM_TDB	
22	414762	mask	USPAT;	2004/03/09 07:49
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
23	63372	pattern\$3 near5 metal	USPAT;	2004/03/09 07:50
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
24	7500	(pattern\$3 near5 metal) near10 mask	USPAT;	2004/03/09 07:50
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
L			IBM_TDB	l

•				
25	71756	(common counter) adj (electrode line)	USPAT; US-PGPUB;	2004/03/09 07:50
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
26	7	((pattern\$3 near5 metal) near10 mask) same ((common counter)	USPAT;	2004/03/09 07:50
20	/	adj (electrode line)) same ((gate scan\$4) adj (line wir\$3))	US-PGPUB;	2007/03/03 07.30
		adj (electrode line)) same ((gate scans+) adj (line wirs5))	EPO; JPO;	į
-			DERWENT;	
1			IBM_TDB	
27	6004	(pattern\$3 near5 metal) near10 semiconductor	USPAT;	2004/03/09 07:51
27	6004	(patterns5 flear5 filetar) flear to semiconductor	US-PGPUB;	2004/03/09 07.31
			EPO; JPO;	
			DERWENT;	
	İ		IBM_TDB	
28	2	(((pattern\$3 near5 metal) near10 mask) same ((common counter)	USPAT;	2004/03/09 07:53
20		adj (electrode line)) same ((gate scan\$4) adj (line wir\$3))) and	US-PGPUB;	2007/03/03/03/07.33
		((pattern\$3 near5 metal) near10 semiconductor)	EPO; JPO;	
		((patterna) nears metar) near to semiconductor)	DERWENT;	
			IBM_TDB	
29	39	lee-yun-bok.in.	USPAT;	2004/03/09 07:53
29	39	lee-yuii-bok.iii.	US-PGPUB;	2004/03/09 07.33
}			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
31	0	349/187.ccls. and lee-yun-bok.in.	USPAT:	2004/03/09 07:53
31		349/107.ccis. drid ice-ydri-bok.iii.	US-PGPUB;	2007/03/05 07.33
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
30	10	349/141.ccls. and lee-yun-bok.in.	USPAT;	2004/03/09 07:53
30	10	5 15/1 11:003. Gild ICC yall box.iii.	US-PGPUB;	2007/03/03 07.33
			EPO; JPO;	
			DERWENT;	
			IBM TDB	